



Docket No. 8017-1169
Appln. No. 10/536,993

AMENDMENTS TO THE CLAIMS:

This listing of claims will replace all prior versions, and listings, of claims in the application:

LISTING OF CLAIMS:

1. (original) A semiconductor device comprising connection plug wherein a nanomaterial is substantially uniformly disposed in a section of the connection plug formed from a metal.

2. (original) A semiconductor device comprising an interconnection wherein a nanomaterial is substantially uniformly formed on a bottom surface of the interconnection formed from a metal.

3. (original) The semiconductor device according to claim 1, wherein the nanomaterial is a fibrous carbon nanomaterial, a particle-like carbon nanomaterial or a thin silicon wire.

4. (original) The semiconductor device according to claim 2, wherein the nanomaterial is a fibrous carbon nanomaterial, a granular particle-like carbon nanomaterial or a thin silicon wire.

5. (original) The semiconductor device according to claim 1, wherein the nanomaterial is oriented substantially perpendicularly to a substrate.

6. (original) The semiconductor device according to claim 2, wherein the nanomaterial is oriented substantially perpendicularly to a substrate.

7. (original) The semiconductor device according to claim 1, wherein the nanomaterial is provided in the whole connection plug.

8. (original) The semiconductor device according to claim 2, wherein the nanomaterial is provided up to the vicinity of a top surface of the interconnection.

9. (original) The semiconductor device according to claim 1, wherein the metal is formed by an MOCVD method or a plating method.

10. (original) The semiconductor device according to claim 2, wherein the metal is formed by an MOCVD method or a plating method.

11-19. (canceled)

20. (original) The semiconductor device according to claim 1, wherein the connection plug formed from a metal is formed by a plating method which involves using a plating liquid containing a nanomaterial.

21. (original) The semiconductor device according to claim 2, wherein the interconnection formed from a metal is formed by a plating method which involves using a plating liquid containing a nanomaterial.

22-26. (canceled)